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What is "[Embedded - Microcontrollers](#)"?

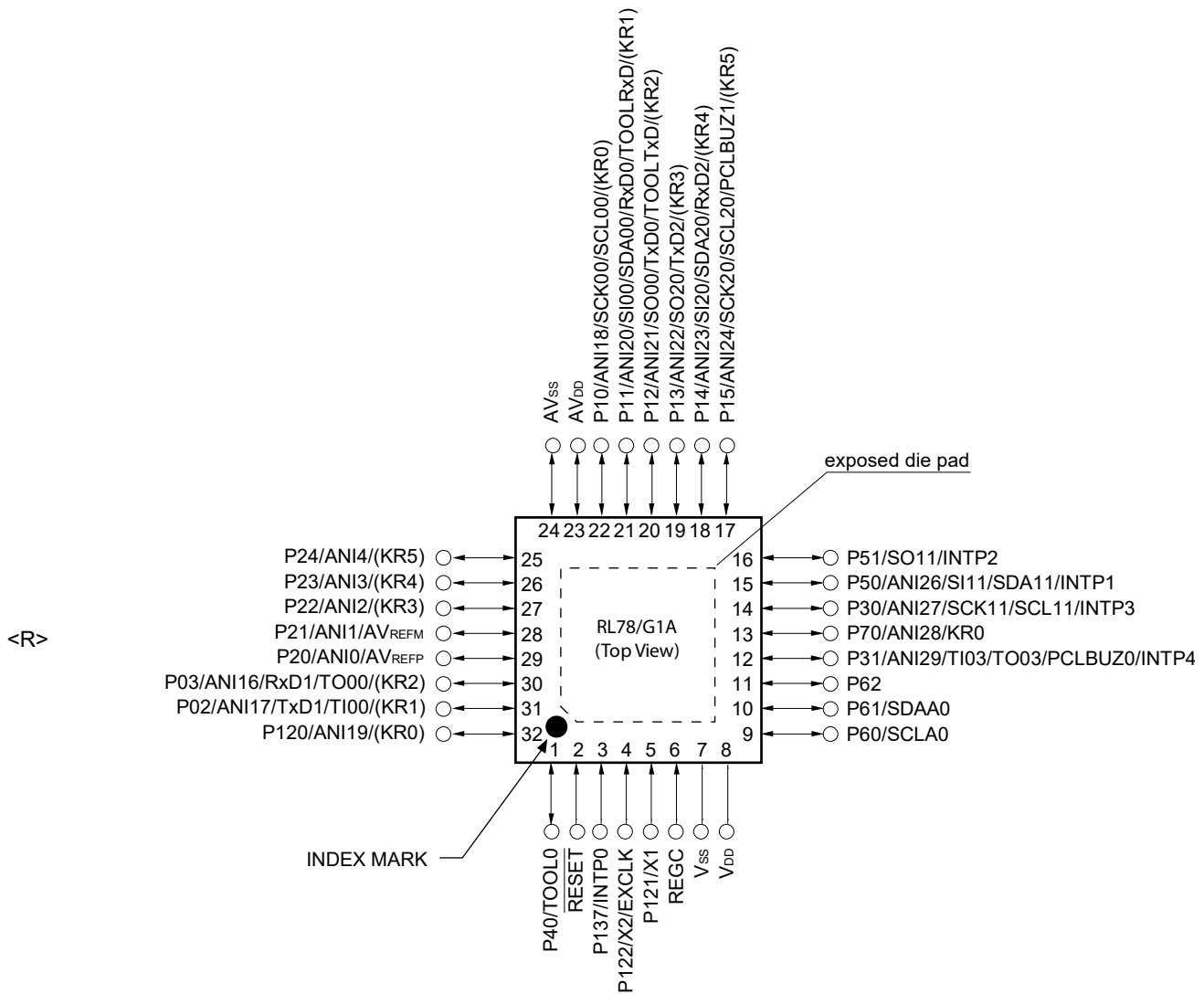
"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "[Embedded - Microcontrollers](#)"

Details	
Product Status	Active
Core Processor	RL78
Core Size	16-Bit
Speed	32MHz
Connectivity	CSI, I ² C, LINbus, UART/USART
Peripherals	DMA, LVD, POR, PWM, WDT
Number of I/O	46
Program Memory Size	64KB (64K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	4K x 8
Voltage - Supply (Vcc/Vdd)	1.6V ~ 3.6V
Data Converters	A/D 28x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	64-LQFP
Supplier Device Package	64-LFQFP (10x10)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f10elegfb-v0

1.3.2 32-pin products

- 32-pin plastic HWQFN (5 × 5 mm, 0.5 mm pitch)



Caution Connect the REGC pin to V_{SS} via a capacitor (0.47 to 1 μF).

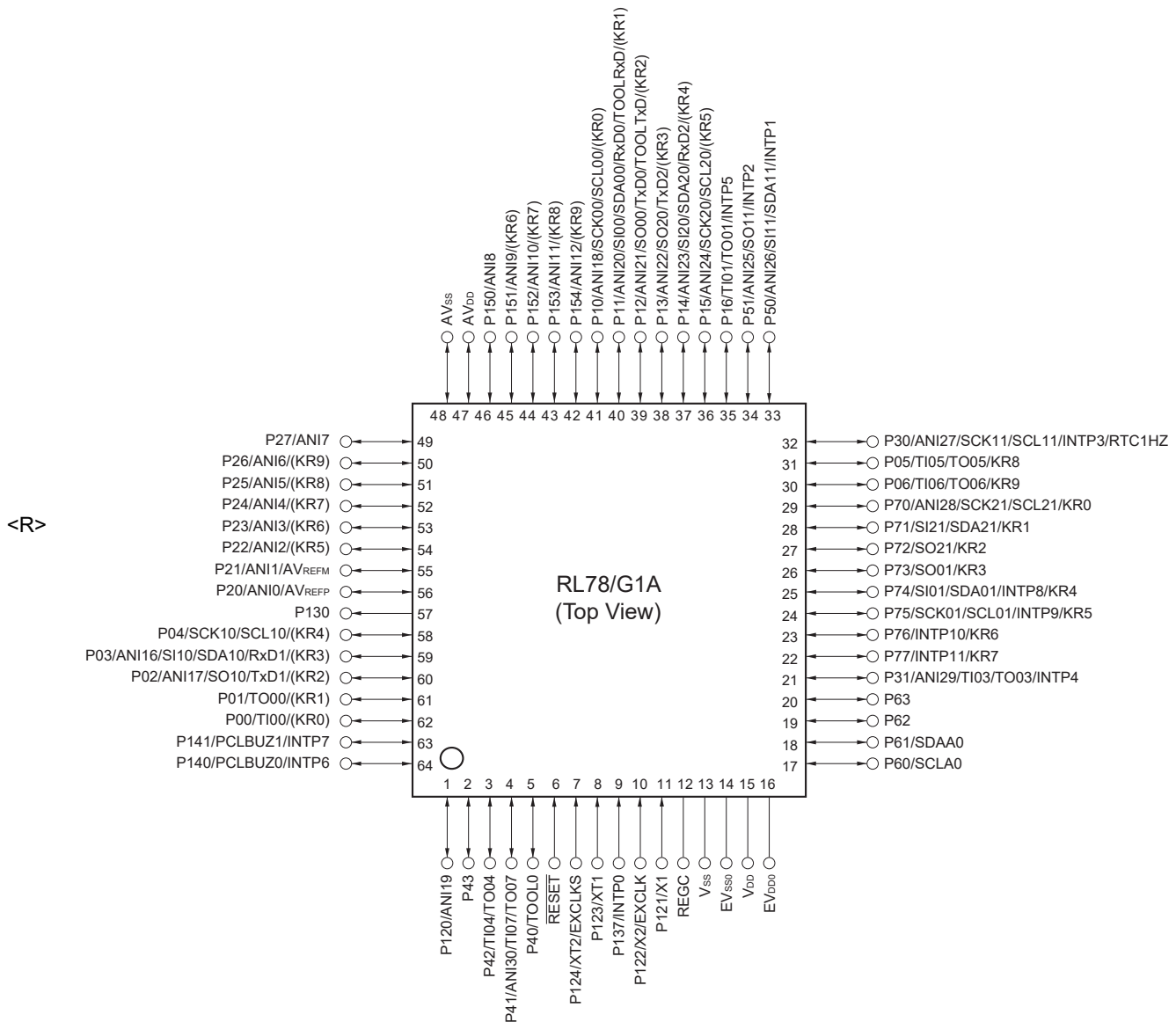
Remarks 1. For pin identification, see 1.4 Pin Identification.

2. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR).

3. It is recommended to connect an exposed die pad to V_{SS}.

1.3.4 64-pin products

- 64-pin plastic LQFP (10 × 10 mm, 0.5 mm pitch)

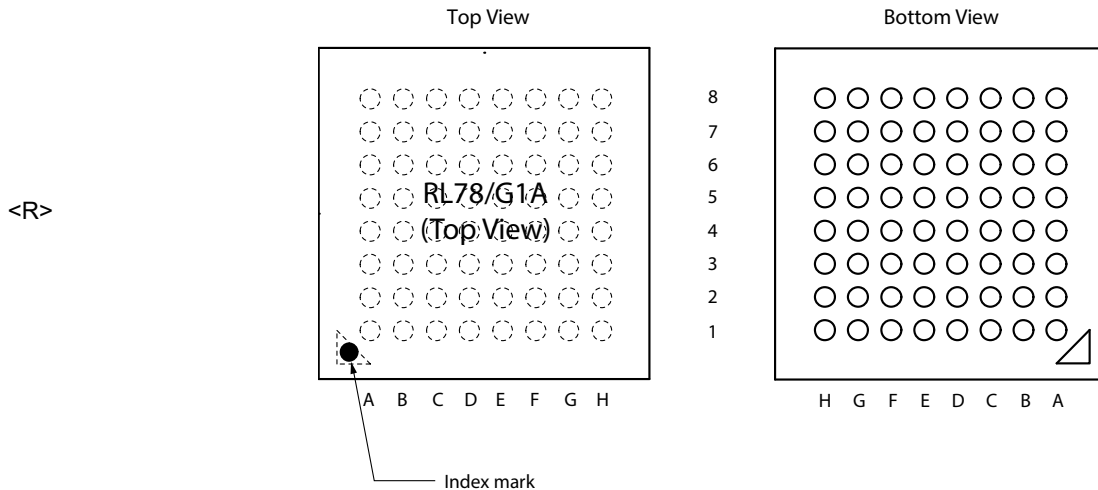


- Cautions 1.** Make EV_{SS0} pin the same potential as V_{SS} pin.
- Make V_{DD} pin the potential that is higher than EV_{DD0} pin.
 - Connect the REGC pin to V_{SS} via a capacitor (0.47 to 1 μF).

Remarks 1. For pin identification, see 1.4 Pin Identification.

- When using the microcontroller for an application where the noise generated inside the microcontroller must be reduced, it is recommended to supply separate powers to the V_{DD} and EV_{DD0} pins and connect the V_{SS} and EV_{SS0} pins to separate ground lines.
- Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR).

- 64-pin plastic VFBGA (4 × 4 mm, 0.4 mm pitch)

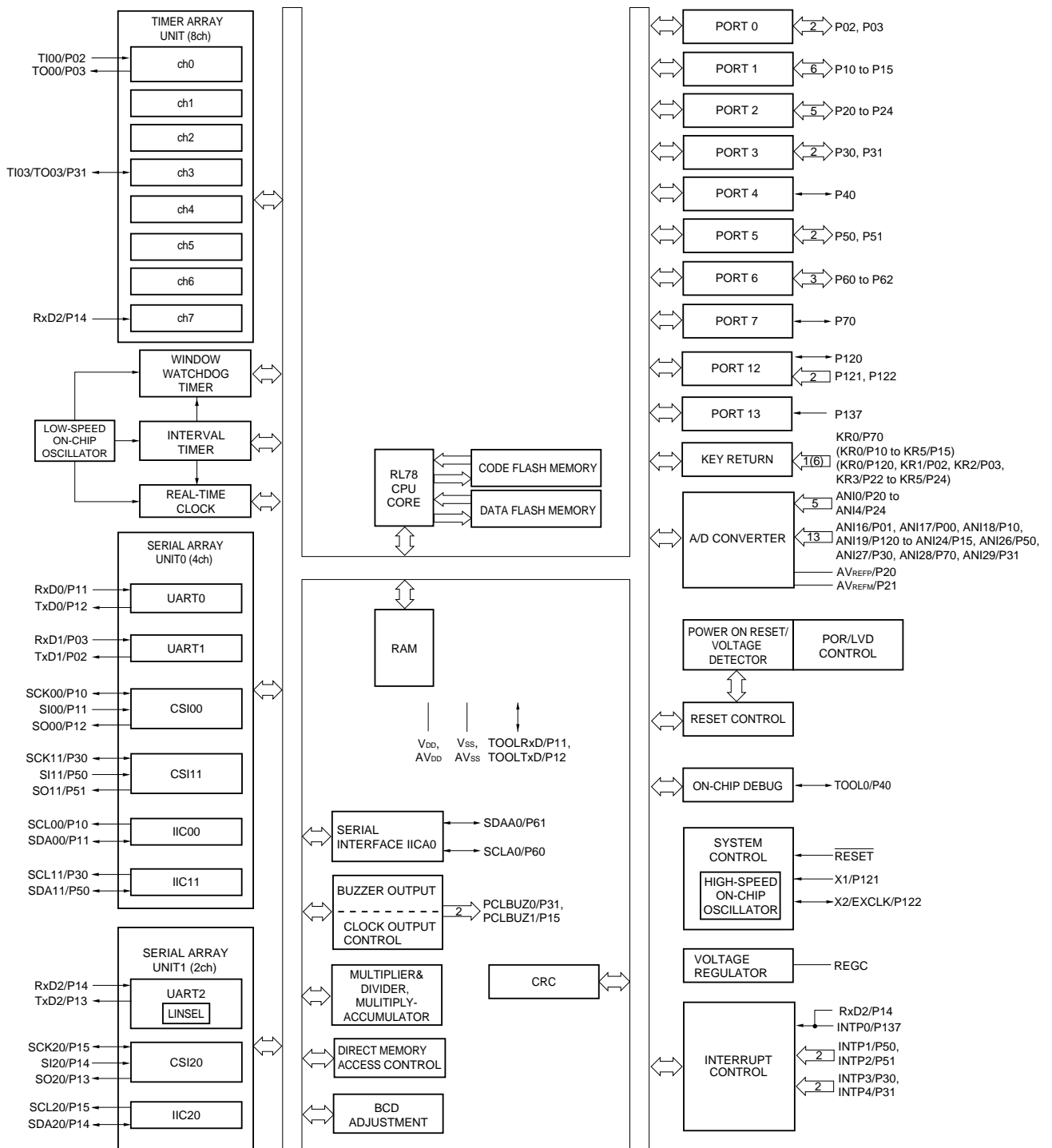


Pin No.	Name	Pin No.	Name	Pin No.	Name	Pin No.	Name
A1	P05/TI05/TO05/KR8	C1	P51/ANI25/SO11 /INTP2	E1	P153/ANI11/(KR8)	G1	AV _{DD}
A2	P30/ANI27/SCK11 /SCL11/INTP3 /RTC1HZ	C2	P71/SI21/SDA21/KR1	E2	P154/ANI12/(KR9)	G2	P25/ANI5/(KR8)
A3	P70/ANI28/SCK21 /SCL21/KR0	C3	P74/SI01/SDA01 /INTP8/KR4	E3	P10/ANI18/SCK00 /SCL00/(KR0)	G3	P24/ANI4/(KR7)
A4	P75/SCK01/SCL01 /INTP9/KR5	C4	P16/TI01/TO01/INTP5	E4	P11/ANI20/SI00 /SDA00/RxD0 /TOOLRxD/(KR1)	G4	P22/ANI2/(KR5)
A5	P77/INTP11/KR7	C5	P15/ANI24/SCK20 /SCL20/(KR5)	E5	P03/ANI16/SI10 /SDA10/RxD1/(KR3)	G5	P130
A6	P61/SDAA0	C6	P63	E6	P41/ANI30/TI07/TO07	G6	P02/ANI17/SO10/TxD1 //(KR2)
A7	P60/SCLA0	C7	V _{SS}	E7	RESET	G7	P00/TI00/(KR0)
A8	EV _{DD0}	C8	P121/X1	E8	P137/INTP0	G8	P124/XT2/EXCLKS
B1	P50/ANI26 /SI11 /SDA11/INTP1	D1	P13/ANI22/SO20 /TxD2/(KR3)	F1	P150/ANI8	H1	AV _{SS}
B2	P72/SO21/KR2	D2	P06/TI06/TO06/KR9	F2	P151/ANI9/(KR6)	H2	P27/ANI7
B3	P73/SO01/KR3	D3	P12/ANI21/SO00 /TxD0/TOOLTxD/(KR2)	F3	P152/ANI10/(KR7)	H3	P26/ANI6/(KR9)
B4	P76/INTP10/KR6	D4	P14/ANI23/SI20/ SDA20/RxD2/(KR4)	F4	P21/ANI1/AV _{REFM}	H4	P23/ANI3/(KR6)
B5	P31/ANI29/TI03/TO03 /INTP4	D5	P42/TI04/TO04	F5	P04/SCK10/SCL10 //(KR4)	H5	P20/ANI0/AV _{REFP}
B6	P62	D6	P40/TOOL0	F6	P43	H6	P141/PCLBUZ1/INTP7
B7	V _{DD}	D7	REGC	F7	P01/TO00/(KR1)	H7	P140/PCLBUZ0/INTP6
B8	EV _{SS0}	D8	P122/X2/EXCLK	F8	P123/XT1	H8	P120/ANI19

- Cautions**
1. Make EV_{SS0} pin the same potential as V_{SS} pin.
 2. Make V_{DD} pin the potential that is higher than EV_{DD0} pin.
 3. Connect the REGC pin to V_{SS} via a capacitor (0.47 to 1 μF).

- Remarks**
1. For pin identification, see 1.4 Pin Identification.
 2. When using the microcontroller for an application where the noise generated inside the microcontroller must be reduced, it is recommended to supply separate powers to the V_{DD} and EV_{DD0} pins and connect the V_{SS} and EV_{SS0} pins to separate ground lines.
 3. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR).

<R> 1.5.2 32-pin products



Remark Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR).

2.3 DC Characteristics

2.3.1 Pin characteristics

(T_A = -40 to +85°C, 1.6 V ≤ AV_{DD} ≤ V_{DD} ≤ 3.6 V, 1.6 V ≤ EV_{DD0} ≤ V_{DD} ≤ 3.6 V, V_{SS} = EV_{SS0} = 0 V) (1/5)

Items	Symbol	Conditions	MIN.	TYP.	MAX.	Unit	
Output current, high ^{Note 1}	I _{OH1}	Per pin for P00 to P06, P10 to P16, P30, P31, P40 to P43, P50, P51, P70 to P77, P120, P130, P140, P141	1.6 V ≤ EV _{DD0} ≤ 3.6 V			-10.0 ^{Note 2}	mA
		Total of P00 to P04, P40 to P43, P120, P130, P140, P141 (When duty ≤ 70% ^{Note 3})	2.7 V ≤ EV _{DD0} ≤ 3.6 V			-10.0	mA
			1.8 V ≤ EV _{DD0} < 2.7 V			-5.0	mA
			1.6 V ≤ EV _{DD0} < 1.8 V			-2.5	mA
		Total of P05, P06, P10 to P16, P30, P31, P50, P51, P70 to P77, (When duty ≤ 70% ^{Note 3})	2.7 V ≤ EV _{DD0} ≤ 3.6 V			-19.0	mA
			1.8 V ≤ EV _{DD0} < 2.7 V			-10.0	mA
			1.6 V ≤ EV _{DD0} < 1.8 V			-5.0	mA
	Total of all pins (When duty ≤ 70% ^{Note 3})	1.6 V ≤ EV _{DD0} ≤ 3.6 V			-29.0	mA	
	I _{OH2}	Per pin for P20 to P27, P150 to P154	1.6 V ≤ AV _{DD} ≤ 3.6 V			-0.1 ^{Note 2}	mA
		Total of all pins (When duty ≤ 70% ^{Note 3})	1.6 V ≤ AV _{DD} ≤ 3.6 V			-1.3	mA

- Notes**
- Value of current at which the device operation is guaranteed even if the current flows from the EV_{DD0}, V_{DD} pins to an output pin.
 - However, do not exceed the total current value.
 - Specification under conditions where the duty factor ≤ 70%.

The output current value that has changed to the duty factor > 70% the duty ratio can be calculated with the following expression (when changing the duty factor from 70% to n%).

- Total output current of pins = (I_{OH} × 0.7)/(n × 0.01)
 <Example> Where n = 80% and I_{OH} = -10.0 mA
 Total output current of pins = (-10.0 × 0.7)/(80 × 0.01) ≅ -8.7 mA

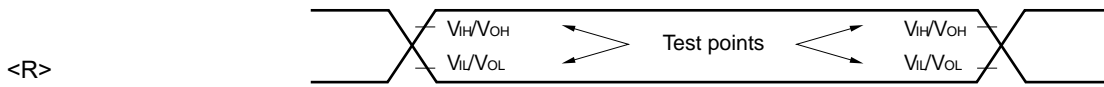
However, the current that is allowed to flow into one pin does not vary depending on the duty factor. A current higher than the absolute maximum rating must not flow into one pin.

Caution P00, P02 to P04, P10 to P15, P43, P50, P71, and P74 do not output high level in N-ch open-drain mode.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

2.5 Peripheral Functions Characteristics

AC Timing Test Points



2.5.1 Serial array unit

(1) During communication at same potential (UART mode)

(T_A = -40 to +85°C, 1.6 V ≤ EV_{DD0} ≤ V_{DD} ≤ 3.6 V, V_{SS} = EV_{SS0} = 0 V)

Parameter	Symbol	Conditions	HS ^{Note 1}		LS ^{Note 2}		LV ^{Note 3}		Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Transfer rate ^{Note 4}		2.4 V ≤ EV _{DD} ≤ 3.6 V		f _{MCK} /6		f _{MCK} /6		f _{MCK} /6	bps
		Theoretical value of the maximum transfer rate f _{MCK} = f _{CLK} ^{Note 6}		5.3 ^{Note 5}		1.3		0.6	Mbps
		1.8 V ≤ EV _{DD} ≤ 3.6 V		f _{MCK} /6		f _{MCK} /6		f _{MCK} /6	bps
		Theoretical value of the maximum transfer rate f _{MCK} = f _{CLK} ^{Note 6}		5.3 ^{Note 5}		1.3		0.6	Mbps
		1.7 V ≤ EV _{DD} ≤ 3.6 V		f _{MCK} /6		f _{MCK} /6		f _{MCK} /6	bps
		Theoretical value of the maximum transfer rate f _{MCK} = f _{CLK} ^{Note 6}		5.3 ^{Note 5}		1.3 ^{Note 5}		0.6	Mbps
		1.6 V ≤ EV _{DD} ≤ 3.6 V		-		f _{MCK} /6		f _{MCK} /6	bps
		Theoretical value of the maximum transfer rate f _{MCK} = f _{CLK} ^{Note 6}		-		1.3 ^{Note 5}		0.6	Mbps

- Notes 1.** HS is condition of HS (high-speed main) mode.
2. LS is condition of LS (low-speed main) mode.
3. LV is condition of LV (low-voltage main) mode.
4. Transfer rate in the SNOOZE mode is 4800 bps.
5. The following conditions are required for low-voltage interface when EV_{DD0} < V_{DD}.
 2.4 V ≤ EV_{DD0} < 2.7 V : MAX. 2.6 Mbps
 1.8 V ≤ EV_{DD0} < 2.4 V : MAX. 1.3 Mbps
 1.6 V ≤ EV_{DD0} < 1.8 V : MAX. 0.6 Mbps
6. f_{CLK} in each operating mode is as below.
 HS (high-speed main) mode: f_{CLK} = 32 MHz
 LS (low-speed main) mode: f_{CLK} = 8 MHz
 LV (low-voltage main) mode: f_{CLK} = 4 MHz

Caution Select the normal input buffer for the RxDq pin and the normal output mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg).

(4) During communication at same potential (CSI mode) (slave mode, SCKp... external clock input)

(T_A = -40 to +85°C, 1.6 V ≤ EV_{DD0} ≤ V_{DD} ≤ 3.6 V, V_{SS} = EV_{SS0} = 0 V)

Parameter	Symbol	Conditions		HS ^{Note 1}		LS ^{Note 2}		LV ^{Note 3}		Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time ^{Note 4}	t _{KCY2}	2.7 V ≤ EV _{DD0} ≤ 3.6 V	16 MHz < f _{MCK}	8/f _{MCK}		–		–		ns
			f _{MCK} ≤ 16 MHz	6/f _{MCK}		6/f _{MCK}		6/f _{MCK}		ns
		2.4 V ≤ EV _{DD0} ≤ 3.6 V		6/f _{MCK} and 500ns		6/f _{MCK} and 500ns		6/f _{MCK} and 500ns		ns
		1.8 V ≤ EV _{DD0} ≤ 3.6 V		6/f _{MCK} and 750ns		6/f _{MCK} and 750ns		6/f _{MCK} and 750ns		ns
		1.7 V ≤ EV _{DD0} ≤ 3.6 V		6/f _{MCK} and 1500ns		6/f _{MCK} and 1500ns		6/f _{MCK} and 1500ns		ns
1.6 V ≤ EV _{DD0} ≤ 3.6 V			–		6/f _{MCK} and 1500ns		6/f _{MCK} and 1500ns		ns	
SCKp high-/low-level width	t _{KH2} , t _{KL2}	2.7 V ≤ EV _{DD0} ≤ 3.6 V		t _{KCY2} /2 –8		t _{KCY2} /2 –8		t _{KCY2} /2 –8		ns
		1.8 V ≤ EV _{DD0} ≤ 3.6 V		t _{KCY2} /2 –18		t _{KCY2} /2 –18		t _{KCY2} /2 –18		ns
		1.7 V ≤ EV _{DD0} ≤ 3.6 V		t _{KCY2} /2 –66		t _{KCY2} /2 –66		t _{KCY2} /2 –66		ns
		1.6 V ≤ EV _{DD0} ≤ 3.6 V			–	t _{KCY2} /2 –66		t _{KCY2} /2 –66		ns
Slp setup time (to SCKp↑) ^{Note 5}	t _{SIK2}	2.7 V ≤ EV _{DD0} ≤ 3.6 V		1/f _{MCK} +20		1/f _{MCK} +30		1/f _{MCK} +30		ns
		1.8 V ≤ EV _{DD0} ≤ 3.6 V		1/f _{MCK} +30		1/f _{MCK} +30		1/f _{MCK} +30		ns
		1.7 V ≤ EV _{DD0} ≤ 3.6 V		1/f _{MCK} +40		1/f _{MCK} +40		1/f _{MCK} +40		ns
		1.6 V ≤ EV _{DD0} ≤ 3.6 V			–	1/f _{MCK} +40		1/f _{MCK} +40		ns
Slp hold time (from SCKp↑) ^{Note 5}	t _{SIK2}	1.8 V ≤ EV _{DD0} ≤ 3.6 V		1/f _{MCK} +31		1/f _{MCK} +31		1/f _{MCK} +31		ns
		1.7 V ≤ EV _{DD0} ≤ 3.6 V		1/f _{MCK} +250		1/f _{MCK} +250		1/f _{MCK} +250		ns
		1.6 V ≤ EV _{DD0} ≤ 3.6 V			–	1/f _{MCK} +250		1/f _{MCK} +250		ns
Delay time from SCKp↓ to SOp output ^{Note 6}	t _{KSO2}	C = 30 pF ^{Note 7}	2.7 V ≤ EV _{DD0} ≤ 3.6 V		2/f _{MCK} +44		2/f _{MCK} +110		2/f _{MCK} +110	ns
			2.4 V ≤ EV _{DD0} ≤ 3.6 V		2/f _{MCK} +75		2/f _{MCK} +110		2/f _{MCK} +110	ns
			1.8 V ≤ EV _{DD0} ≤ 3.6 V		2/f _{MCK} +110		2/f _{MCK} +110		2/f _{MCK} +110	ns
			1.7 V ≤ EV _{DD0} ≤ 3.6 V		2/f _{MCK} +220		2/f _{MCK} +220		2/f _{MCK} +220	ns
			1.6 V ≤ EV _{DD0} ≤ 3.6 V			–	2/f _{MCK} +220		2/f _{MCK} +220	ns

(Note, Caution and Remark are listed on the next page.)

(7) Communication at different potential (2.5 V) (CSI mode) (master mode, SCKp... internal clock output, corresponding CSI00 only)

(T_A = -40 to +85°C, 2.7 V ≤ EV_{DD0} ≤ V_{DD} ≤ 3.6 V, V_{SS} = EV_{SS0} = 0 V)

Parameter	Symbol	Conditions	HS ^{Note 1}		LS ^{Note 2}		LV ^{Note 3}		Unit	
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.		
SCKp cycle time	t _{KCY1}	2.7 V ≤ EV _{DD0} ≤ 3.6 V, 2.3 V ≤ V _b ≤ 2.7 V, C _b = 20 pF, R _b = 2.7 kΩ	t _{KCY1} ≥ 2/f _{CLK}	300		1150		1150	ns	
SCKp high-level width	t _{KH1}	2.7 V ≤ EV _{DD0} ≤ 3.6 V, 2.3 V ≤ V _b ≤ 2.7 V, C _b = 20 pF, R _b = 2.7 kΩ	t _{KCY1} /2 –	120		t _{KCY1} /2 –	120	t _{KCY1} /2 –	120	ns
SCKp low-level width	t _{KL1}	2.7 V ≤ EV _{DD0} ≤ 3.6 V, 2.3 V ≤ V _b ≤ 2.7 V, C _b = 20 pF, R _b = 2.7 kΩ	t _{KCY1} /2 –	10		t _{KCY1} /2 –	50	t _{KCY1} /2 –	50	ns
Slp setup time (to SCKp↑) ^{Note 4}	t _{SIK1}	2.7 V ≤ EV _{DD0} ≤ 3.6 V, 2.3 V ≤ V _b ≤ 2.7 V, C _b = 20 pF, R _b = 2.7 kΩ		121		479		479	ns	
Slp hold time (from SCKp↑) ^{Note 4}	t _{KSI1}	2.7 V ≤ EV _{DD0} ≤ 3.6 V, 2.3 V ≤ V _b ≤ 2.7 V, C _b = 20 pF, R _b = 2.7 kΩ		10		10		10	ns	
Delay time from SCKp↓ to SO _p output ^{Note 4}	t _{KSO1}	2.7 V ≤ EV _{DD0} ≤ 3.6 V, 2.3 V ≤ V _b ≤ 2.7 V, C _b = 20 pF, R _b = 2.7 kΩ			130		130		130	ns
Slp setup time (to SCKp↓) ^{Note 5}	t _{SIK1}	2.7 V ≤ EV _{DD0} ≤ 3.6 V, 2.3 V ≤ V _b ≤ 2.7 V, C _b = 20 pF, R _b = 2.7 kΩ		33		110		110	ns	
Slp hold time (from SCKp↓) ^{Note 5}	t _{KSI1}	2.7 V ≤ EV _{DD0} ≤ 3.6 V, 2.3 V ≤ V _b ≤ 2.7 V, C _b = 20 pF, R _b = 2.7 kΩ		10		10		10	ns	
Delay time from SCKp↑ to SO _p output ^{Note 5}	t _{KSO1}	2.7 V ≤ EV _{DD0} ≤ 3.6 V, 2.3 V ≤ V _b ≤ 2.7 V, C _b = 20 pF, R _b = 2.7 kΩ			10		10		10	ns

- Notes**
1. HS is condition of HS (high-speed main) mode.
 2. LS is condition of LS (low-speed main) mode.
 3. LV is condition of LV (low-voltage main) mode.
 4. When DAP_{mn} = 0 and CKP_{mn} = 0, or DAP_{mn} = 1 and CKP_{mn} = 1.
 5. When DAP_{mn} = 0 and CKP_{mn} = 1, or DAP_{mn} = 1 and CKP_{mn} = 0.

Caution Select the TTL input buffer for the Slp pin and the N-ch open drain output (V_{DD} tolerance (When 25- to 48-pin products)/EV_{DD} tolerance (When 64-pin products)) mode for the SO_p pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

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- Remarks**
1. R_b[Ω]: Communication line (SCKp, SO_p) pull-up resistance, C_b[F]: Communication line (SCKp, SO_p) load capacitance, V_b[V]: Communication line voltage
 2. p: CSI number (p = 00), m: Unit number (m = 0), n: Channel number (n = 0),
g: PIM and POM number (g = 1)

(9) Communication at different potential (1.8 V, 2.5 V) (CSI mode) (slave mode, SCKp... external clock input)
(T_A = -40 to +85°C, 1.8 V ≤ EV_{DD0} ≤ V_{DD} ≤ 3.6 V, V_{SS} = EV_{SS0} = 0 V)

Parameter	Symbol	Conditions	HS ^{Note 1}		LS ^{Note 2}		LV ^{Note 3}		Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time ^{Note 4}	t _{KCY2}	2.7 V ≤ EV _{DD0} ≤ 3.6 V, 2.3 V ≤ V _b ≤ 2.7 V	24 MHz < f _{MCK}	20/f _{MCK}		–		–	ns
			20 MHz < f _{MCK} ≤ 24 MHz	16/f _{MCK}		–		–	ns
			16 MHz < f _{MCK} ≤ 20 MHz	14/f _{MCK}		–		–	ns
			8 MHz < f _{MCK} ≤ 16 MHz	12/f _{MCK}		–		–	ns
			4 MHz < f _{MCK} ≤ 8 MHz	8/f _{MCK}		16/f _{MCK}		–	ns
			f _{MCK} ≤ 4 MHz	6/f _{MCK}		10/f _{MCK}		10/f _{MCK}	ns
		1.8 V ≤ EV _{DD0} < 3.3 V, 1.6 V ≤ V _b ≤ 2.0 V ^{Note 5}	24 MHz < f _{MCK}	48/f _{MCK}		–		–	ns
			20 MHz < f _{MCK} ≤ 24 MHz	36/f _{MCK}		–		–	ns
			16 MHz < f _{MCK} ≤ 20 MHz	32/f _{MCK}		–		–	ns
			8 MHz < f _{MCK} ≤ 16 MHz	26/f _{MCK}		–		–	ns
			4 MHz < f _{MCK} ≤ 8 MHz	16/f _{MCK}		16/f _{MCK}		–	ns
f _{MCK} ≤ 4 MHz	10/f _{MCK}		10/f _{MCK}		10/f _{MCK}	ns			
SCKp high-/low-level width	t _{KH2} , t _{KL2}	2.7 V ≤ EV _{DD0} ≤ 3.6 V, 2.3 V ≤ V _b ≤ 2.7 V	t _{KCY2} /2 – 18		t _{KCY2} /2 – 50		t _{KCY2} /2 – 50	ns	
		1.8 V ≤ EV _{DD0} < 3.3 V, 1.6 V ≤ V _b ≤ 2.0 V ^{Note 5}	t _{KCY2} /2 – 50		t _{KCY2} /2 – 50		t _{KCY2} /2 – 50	ns	
Slp setup time (to SCKp↑) ^{Note 6}	t _{SIK2}	2.7 V ≤ EV _{DD0} ≤ 3.6 V, 2.3 V ≤ V _b ≤ 2.7 V	1/f _{MCK} + 20		1/f _{MCK} + 30		1/f _{MCK} + 30	ns	
		1.8 V ≤ EV _{DD0} < 3.3 V, 1.6 V ≤ V _b ≤ 2.0 V ^{Note 5}	1/f _{MCK} + 30		1/f _{MCK} + 30		1/f _{MCK} + 30	ns	
Slp hold time (from SCKp↑) ^{Note 6}	t _{SIH2}		1/f _{MCK} + 31		1/f _{MCK} + 31		1/f _{MCK} + 31	ns	
Delay time from SCKp↓ to SOp output ^{Note 7}	t _{KSO2}	2.7 V ≤ EV _{DD0} ≤ 3.6 V, 2.3 V ≤ V _b ≤ 2.7 V, C _b = 30 pF, R _b = 2.7 kΩ		2/f _{MCK} + 214		2/f _{MCK} + 573		2/f _{MCK} + 573	ns
		1.8 V ≤ EV _{DD0} < 3.3 V, 1.6 V ≤ V _b ≤ 2.0 V ^{Note 5} , C _b = 30 pF, R _b = 5.5 kΩ		2/f _{MCK} + 573		2/f _{MCK} + 573		2/f _{MCK} + 573	ns

Notes 1. HS is condition of HS (high-speed main) mode.

2. LS is condition of LS (low-speed main) mode.

3. LV is condition of LV (low-voltage main) mode.

4. Transfer rate in the SNOOZE mode : MAX. 1 Mbps

5. Use it with EV_{DD0} ≥ V_b.

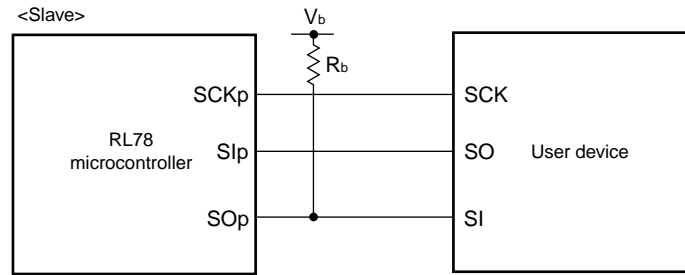
6. When DAP_{mn} = 0 and CKP_{mn} = 0, or DAP_{mn} = 1 and CKP_{mn} = 1. The Slp setup time or Slp hold time becomes “from SCKp↓” when DAP_{mn} = 0 and CKP_{mn} = 1, or DAP_{mn} = 1 and CKP_{mn} = 0.

7. When DAP_{mn} = 0 and CKP_{mn} = 0, or DAP_{mn} = 1 and CKP_{mn} = 1. The delay time to SOp output becomes “from SCKp↑” when DAP_{mn} = 0 and CKP_{mn} = 1, or DAP_{mn} = 1 and CKP_{mn} = 0.

Caution Select the TTL input buffer for the Slp pin and SCKp pin and the N-ch open drain output (V_{DD} tolerance (When 25- to 48-pin products)/EV_{DD} tolerance (When 64-pin products)) mode for the SOp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

<R>

(Remarks are listed on the next page.)

CSI mode connection diagram (during communication at different potential)

- Remarks**
1. $R_b[\Omega]$: Communication line (SO_p) pull-up resistance, $C_b[\text{F}]$: Communication line (SO_p) load capacitance, $V_b[\text{V}]$: Communication line voltage
 2. p: CSI number (p = 00, 10, 20), m: Unit number (m = 0, 1), n: Channel number (n = 00, 02, 10), g: PIM and POM number (g = 0, 1)
 3. f_{mck} : Serial array unit operation clock frequency
(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn).
m: Unit number, n: Channel number (mn = 00, 02, 10))
 4. CSI01, CSI11, and CSI21 cannot communicate at different potential. Use other CSI for communication at different potential.

(10) Communication at different potential (1.8 V, 2.5 V) (simplified I²C mode) (1/2)**(T_A = -40 to +85°C, 1.8 V ≤ EV_{DD0} ≤ V_{DD} ≤ 3.6 V, V_{SS} = EV_{SS0} = 0 V)**

Parameter	Symbol	Conditions	HS ^{Note 1}		LS ^{Note 2}		LV ^{Note 3}		Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCLr clock frequency	f _{SCL}	2.7 V ≤ EV _{DD0} ≤ 3.6 V, 2.3 V ≤ V _b ≤ 2.7 V, C _b = 50 pF, R _b = 2.7 kΩ		1000 ^{Note 4}		300 ^{Note 4}		300 ^{Note 4}	kHz
		2.7 V ≤ EV _{DD0} ≤ 3.6 V, 2.3 V ≤ V _b ≤ 2.7 V, C _b = 100 pF, R _b = 2.7 kΩ		400 ^{Note 4}		300 ^{Note 4}		300 ^{Note 4}	kHz
		1.8 V ≤ EV _{DD0} < 3.3 V, 1.6 V ≤ V _b ≤ 2.0 V ^{Note 5} , C _b = 100 pF, R _b = 5.5 kΩ		300 ^{Note 4}		300 ^{Note 4}		300 ^{Note 4}	kHz
Hold time when SCLr = "L"	t _{LOW}	2.7 V ≤ EV _{DD0} ≤ 3.6 V, 2.3 V ≤ V _b ≤ 2.7 V, C _b = 50 pF, R _b = 2.7 kΩ	475		1550		1550		ns
		2.7 V ≤ EV _{DD0} ≤ 3.6 V, 2.3 V ≤ V _b ≤ 2.7 V, C _b = 100 pF, R _b = 2.7 kΩ	1150		1550		1550		ns
		1.8 V ≤ EV _{DD0} < 3.3 V, 1.6 V ≤ V _b ≤ 2.0 V ^{Note 5} , C _b = 100 pF, R _b = 5.5 kΩ	1550		1550		1550		ns
Hold time when SCLr = "H"	t _{HIGH}	2.7 V ≤ EV _{DD0} ≤ 3.6 V, 2.3 V ≤ V _b ≤ 2.7 V, C _b = 50 pF, R _b = 2.7 kΩ	200		610		610		ns
		2.7 V ≤ EV _{DD0} ≤ 3.6 V, 2.3 V ≤ V _b ≤ 2.7 V, C _b = 100 pF, R _b = 2.7 kΩ	600		610		610		ns
		1.8 V ≤ EV _{DD0} < 3.3 V, 1.6 V ≤ V _b ≤ 2.0 V ^{Note 5} , C _b = 100 pF, R _b = 5.5 kΩ	610		610		610		ns

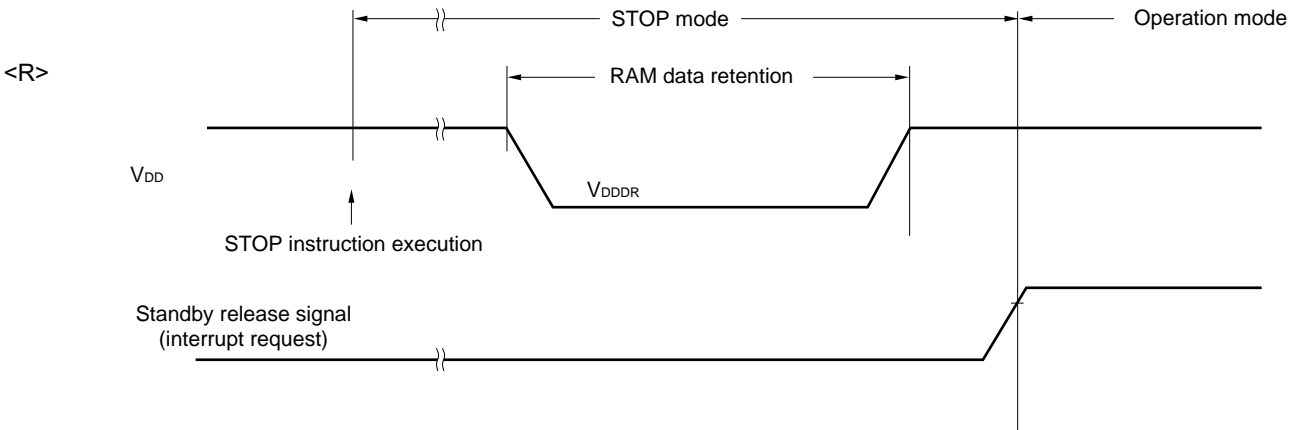
(Notes, Caution and Remarks are listed on the next page.)

<R> 2.7 RAM Data Retention Characteristics

<R> (T_A = -40 to +85°C, V_{SS} = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Data retention supply voltage	V _{DDDR}		1.46 ^{Note}		3.6	V

<R> **Note** This depends on the POR detection voltage. For a falling voltage, data in RAM are retained until the voltage reaches the level that triggers a POR reset but not once it reaches the level at which a POR reset is generated.



<R> 2.8 Flash Memory Programming Characteristics

(T_A = -40 to +85°C, 1.8 V ≤ V_{DD} ≤ 3.6 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
CPU/peripheral hardware clock frequency	f _{CLK}	1.8 V ≤ V _{DD} ≤ 3.6 V	1		32	MHz
Number of code flash rewrites ^{Notes 1, 2}	C _{erwr}	Retained for 20 years T _A = 85°C ^{Note 3}	1,000			Times
Number of data flash rewrites ^{Notes 1, 2}		Retained for 1 years T _A = 25°C ^{Note 3}		1,000,000		
		Retained for 5 years T _A = 85°C ^{Note 3}	100,000			
		Retained for 20 years T _A = 85°C ^{Note 3}	10,000			

- Notes 1.** 1 erase + 1 write after the erase is regarded as 1 rewrite.
The retaining years are until next rewrite after the rewrite.
- 2.** When using flash memory programmer and Renesas Electronics self programming library
- 3.** These are the characteristics of the flash memory and the results obtained from reliability testing by Renesas Electronics Corporation.

($T_A = -40$ to $+105^\circ\text{C}$, $2.4\text{ V} \leq AV_{DD} \leq V_{DD} \leq 3.6\text{ V}$, $2.4\text{ V} \leq EV_{DD0} \leq V_{DD} \leq 3.6\text{ V}$, $V_{SS} = EV_{SS0} = 0\text{ V}$) (5/5)

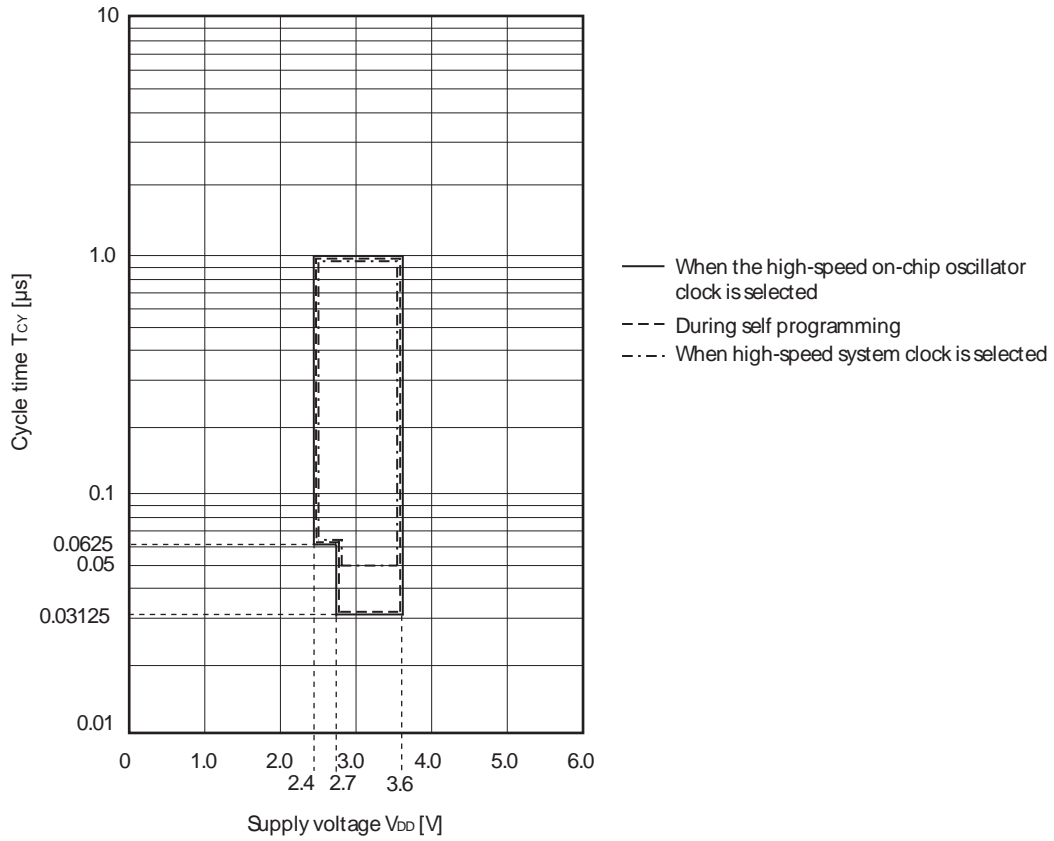
Items	Symbol	Conditions	MIN.	TYP.	MAX.	Unit		
Input leakage current, high	I _{LIH1}	P00 to P06, P10 to P16, P30, P31, P40 to P43, P50, P51, P60 to P63, P70 to P77, P120, P140, P141	V _I = EV _{DD0}		1	μA		
	I _{LIH2}	P137, $\overline{\text{RESET}}$	V _I = V _{DD}		1	μA		
	I _{LIH3}	P121 to P124 (X1, X2, XT1, XT2, EXCLK, EXCLKS)	V _I = V _{DD}	In input port or external clock input	1	μA		
				In resonator connection	10	μA		
I _{LIH4}	P20 to P27, P150 to P154	V _I = AV _{DD}		1	μA			
Input leakage current, low	I _{LIL1}	P00 to P06, P10 to P16, P30, P31, P40 to P43, P50, P51, P60 to P67, P70 to P77, P120, P140, P141	V _I = EV _{SS0}		-1	μA		
	I _{LIL2}	P137, $\overline{\text{RESET}}$	V _I = V _{SS}		-1	μA		
	I _{LIL3}	P121 to P124 (X1, X2, XT1, XT2, EXCLK, EXCLKS)	V _I = V _{SS}	In input port or external clock input	-1	μA		
				In resonator connection	-10	μA		
I _{LIL4}	P20 to P27, P150 to P154	V _I = AV _{SS}		-1	μA			
On-chip pull-up resistance	R _U	P00 to P06, P10 to P16, P30, P31, P40 to P43, P50, P51, P70 to P77, P120, P140, P141	V _I = EV _{SS0} , In input port		10	20	100	kΩ

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

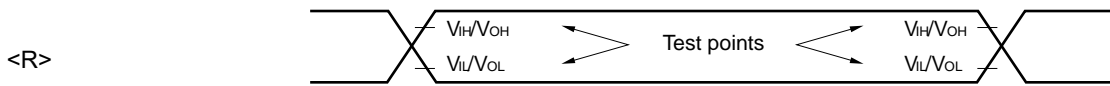
Minimum Instruction Execution Time during Main System Clock Operation

<R>

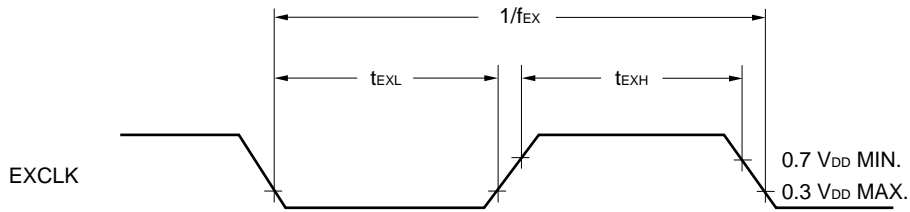
T_{CY} vs V_{DD} (HS (high-speed main) mode)



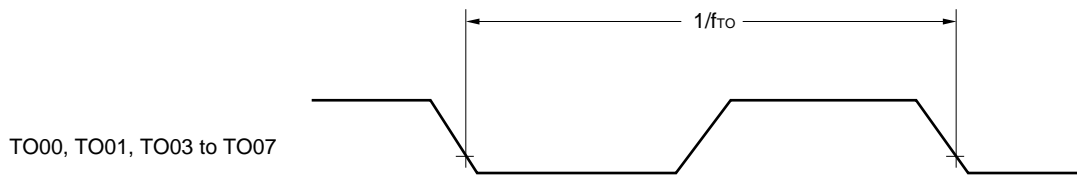
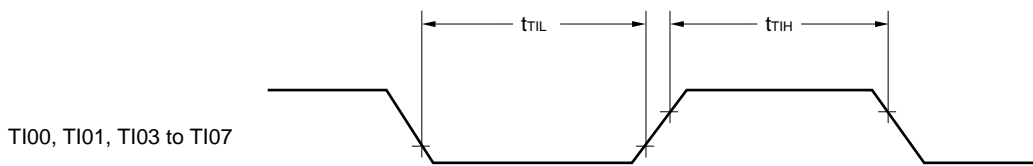
AC Timing Test Points



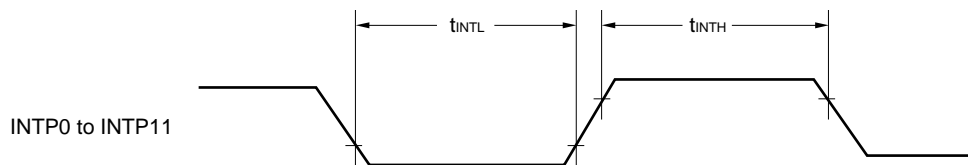
External System Clock Timing



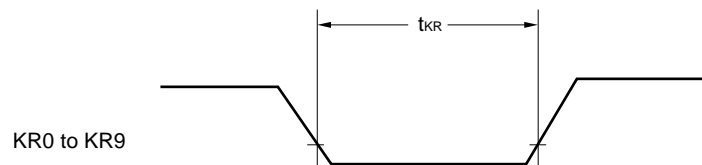
<R> **TI/TO Timing**



Interrupt Request Input Timing



Key Interrupt Input Timing



<R> (3) During communication at same potential (CSI mode) (slave mode, SCKp... external clock input)
 ($T_A = -40$ to $+105^\circ\text{C}$, $2.4\text{ V} \leq \text{EV}_{\text{DD0}} \leq \text{V}_{\text{DD}} \leq 3.6\text{ V}$, $\text{V}_{\text{SS}} = \text{EV}_{\text{SS0}} = 0\text{ V}$)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit	
SCKp cycle time ^{Note 1}	t_{KCY2}	$2.7\text{ V} \leq \text{EV}_{\text{DD0}} \leq 3.6\text{ V}$	$16\text{ MHz} < f_{\text{MCK}}$	$16/f_{\text{MCK}}$		ns	
			$f_{\text{MCK}} \leq 16\text{ MHz}$	$12/f_{\text{MCK}}$		ns	
		$2.4\text{ V} \leq \text{EV}_{\text{DD0}} \leq 3.6\text{ V}$		$12/f_{\text{MCK}}$ and 1000		ns	
SCKp high-/low-level width	t_{KH2} , t_{KL2}	$2.7\text{ V} \leq \text{EV}_{\text{DD0}} \leq 3.6\text{ V}$		$t_{\text{KCY2}}/2-14$		ns	
		$2.4\text{ V} \leq \text{EV}_{\text{DD0}} \leq 3.6\text{ V}$		$t_{\text{KCY2}}/2-16$		ns	
Slp setup time (to SCKp \uparrow) ^{Note 2}	t_{SIK2}	$2.7\text{ V} \leq \text{EV}_{\text{DD0}} \leq 3.6\text{ V}$		$1/f_{\text{MCK}} + 40$		ns	
		$2.4\text{ V} \leq \text{EV}_{\text{DD0}} \leq 3.6\text{ V}$		$1/f_{\text{MCK}} + 60$		ns	
Slp hold time (from SCKp \uparrow) ^{Note 2}	t_{KSI2}	$2.7\text{ V} \leq \text{EV}_{\text{DD0}} \leq 3.6\text{ V}$		$1/f_{\text{MCK}}+62$		ns	
		$2.4\text{ V} \leq \text{EV}_{\text{DD0}} \leq 3.6\text{ V}$		$1/f_{\text{MCK}}+62$		ns	
Delay time from SCKp \downarrow to SOp output ^{Note 3}	t_{KSO2}	$C = 30\text{ pF}$ ^{Note 4}	$2.7\text{ V} \leq \text{EV}_{\text{DD0}} \leq 3.6\text{ V}$			$2/f_{\text{MCK}}+66$	ns
			$2.4\text{ V} \leq \text{EV}_{\text{DD0}} \leq 3.6\text{ V}$				$2/f_{\text{MCK}}+113$

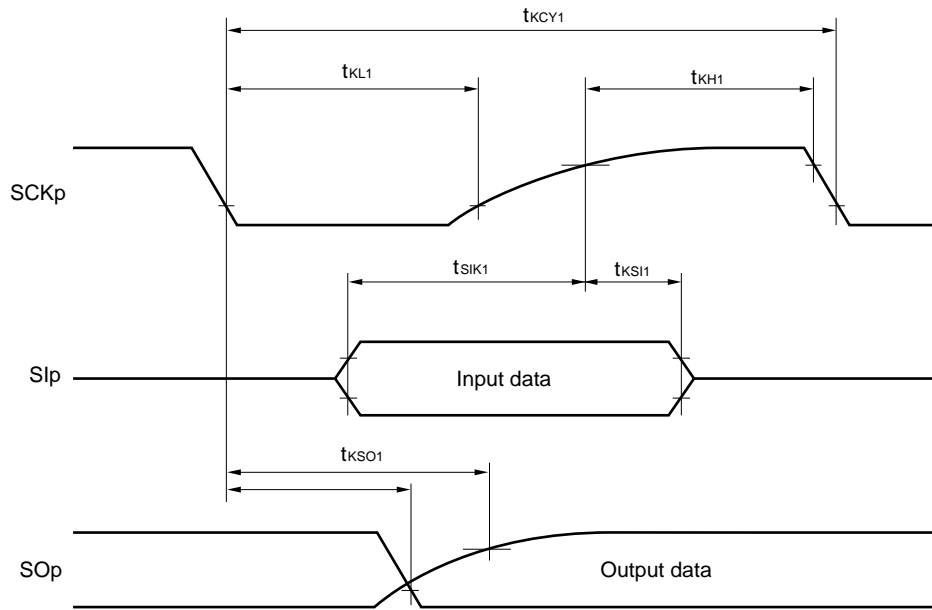
Notes 1. Transfer rate in the SNOOZE mode : MAX. 1 Mbps

- When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The Slp setup time or Slp hold time becomes "from SCKp \downarrow " when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp \uparrow " when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- C is the load capacitance of the SOp output lines.

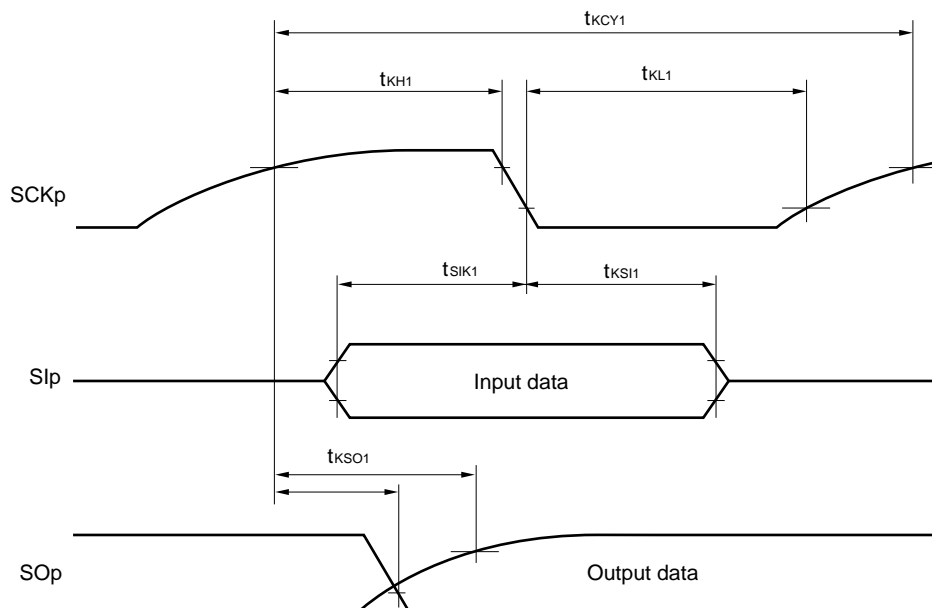
Caution Select the normal input buffer for the Slp pin and SCKp pin and the normal output mode for the SOp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

- Remarks 1.** p: CSI number (p = 00, 01, 10, 11, 20, 21), m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3),
 g: PIM number (g = 0, 1)
- 2.** f_{MCK} : Serial array unit operation clock frequency
 (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,
 n: Channel number (mn = 00 to 03, 10, 11))

**CSI mode serial transfer timing (master mode) (during communication at different potential)
(When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)**



**CSI mode serial transfer timing (master mode) (during communication at different potential)
(When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)**



- Remarks**
1. p: CSI number (p = 00, 10, 20), m: Unit number, n: Channel number (m = 00, 02, 10), g: PIM and POM number (g = 0, 1)
 2. CSI01, CSI11, and CSI21 cannot communicate at different potential. Use other CSI for communication at different potential.

(8) Communication at different potential (1.8 V, 2.5 V) (simplified I²C mode) (1/2)**($T_A = -40$ to $+105^\circ\text{C}$, $2.4\text{ V} \leq EV_{DD0} \leq V_{DD} \leq 3.6\text{ V}$, $V_{SS} = EV_{SS0} = 0\text{ V}$)**

Parameter	Symbol	Conditions	MIN.	MAX.	Unit
SCLr clock frequency	f _{SCL}	2.7 V \leq EV _{DD0} \leq 3.6 V, 2.3 V \leq V _b \leq 2.7 V, C _b = 50 pF, R _b = 2.7 k Ω		400 ^{Note 1}	kHz
		2.7 V \leq EV _{DD0} \leq 3.6 V, 2.3 V \leq V _b \leq 2.7 V, C _b = 100 pF, R _b = 2.7 k Ω		100 ^{Note 1}	kHz
		2.4 V \leq EV _{DD0} < 3.3 V, 1.6 V \leq V _b \leq 2.0 V, C _b = 100 pF, R _b = 5.5 k Ω		100 ^{Note 1}	kHz
Hold time when SCLr = "L"	t _{LOW}	2.7 V \leq EV _{DD0} \leq 3.6 V, 2.3 V \leq V _b \leq 2.7 V, C _b = 50 pF, R _b = 2.7 k Ω	1200		ns
		2.7 V \leq EV _{DD0} \leq 3.6 V, 2.3 V \leq V _b \leq 2.7 V, C _b = 100 pF, R _b = 2.7 k Ω	4600		ns
		2.4 V \leq EV _{DD0} < 3.3 V, 1.6 V \leq V _b \leq 2.0 V, C _b = 100 pF, R _b = 5.5 k Ω	4650		ns
Hold time when SCLr = "H"	t _{HIGH}	2.7 V \leq EV _{DD0} \leq 3.6 V, 2.3 V \leq V _b \leq 2.7 V, C _b = 50 pF, R _b = 2.7 k Ω	500		ns
		2.7 V \leq EV _{DD0} \leq 3.6 V, 2.3 V \leq V _b \leq 2.7 V, C _b = 100 pF, R _b = 2.7 k Ω	2400		ns
		2.4 V \leq EV _{DD0} < 3.3 V, 1.6 V \leq V _b \leq 2.0 V, C _b = 100 pF, R _b = 5.5 k Ω	1830		ns

(Notes, Caution and Remarks are listed on the next page.)

<R> (3) When reference voltage (+) = $AV_{REFP}/ANI0$ ($ADREFP1 = 0$, $ADREFP0 = 1$), reference voltage (-) = $AV_{REFM}/ANI1$ ($ADREFM = 1$), target for conversion: ANI16 to ANI30, internal reference voltage, temperature sensor output voltage

($T_A = -40$ to $+105^\circ\text{C}$, $2.4\text{ V} \leq EV_{DD0} \leq V_{DD} \leq 3.6\text{ V}$, $2.4\text{ V} \leq AV_{REFP} \leq AV_{DD} \leq V_{DD} \leq 3.6\text{ V}$, $V_{SS} = EV_{SS0} = 0\text{ V}$, $AV_{SS} = 0\text{ V}$, Reference voltage (+) = AV_{REFP} , Reference voltage (-) = $AV_{REFM} = 0\text{ V}$)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	R_{ES}		$2.4\text{ V} \leq AV_{REFP} \leq AV_{DD} \leq 3.6\text{ V}$	8		12	bit
Overall error ^{Note 1}	A_{INL}	12-bit resolution	$2.4\text{ V} \leq AV_{REFP} \leq AV_{DD} \leq 3.6\text{ V}$			± 7.0	LSB
Conversion time	t_{CONV}	$ADTYP = 0$, 12-bit resolution	$2.4\text{ V} \leq AV_{REFP} \leq AV_{DD} \leq 3.6\text{ V}$	4.125			μs
Zero-scale error ^{Note 1}	E_{ZS}	12-bit resolution	$2.4\text{ V} \leq AV_{REFP} \leq AV_{DD} \leq 3.6\text{ V}$			± 5.0	LSB
Full-scale error ^{Note 1}	E_{FS}	12-bit resolution	$2.4\text{ V} \leq AV_{REFP} \leq AV_{DD} \leq 3.6\text{ V}$			± 5.0	LSB
Integral linearity error ^{Note 1}	I_{LE}	12-bit resolution	$2.4\text{ V} \leq AV_{REFP} \leq AV_{DD} \leq 3.6\text{ V}$			± 3.0	LSB
Differential linearity error ^{Note 1}	D_{LE}	12-bit resolution	$2.4\text{ V} \leq AV_{REFP} \leq AV_{DD} \leq 3.6\text{ V}$			± 2.0	LSB
Analog input voltage	V_{AIN}			0.		AV_{REFP} and EV_{DD0}	V
		Internal reference voltage ($2.4\text{ V} \leq V_{DD} \leq 3.6\text{ V}$, HS (high-speed main) mode)			V_{BGR} ^{Note 2}		V
		Temperature sensor output voltage ($2.4\text{ V} \leq V_{DD} \leq 3.6\text{ V}$, HS (high-speed main) mode)			V_{TMPS25} ^{Note 2}		

Notes 1. Excludes quantization error ($\pm 1/2$ LSB).

2. See 3.6.2 Temperature sensor, internal reference voltage output characteristics.

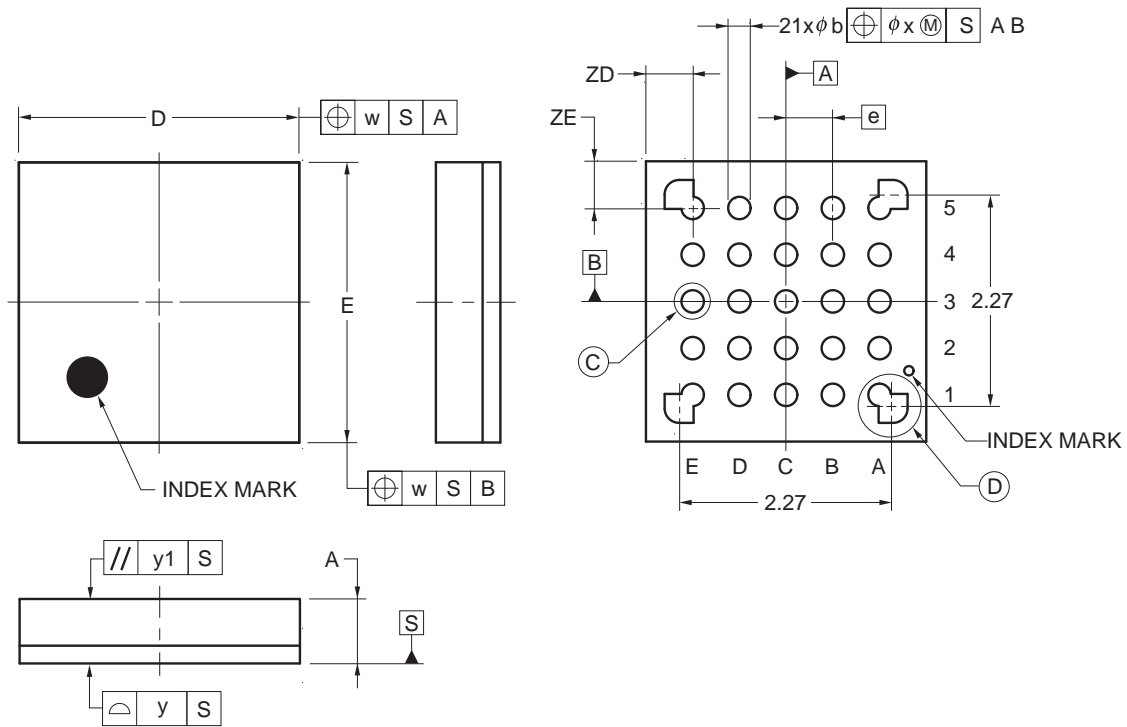
4. PACKAGE DRAWINGS

4.1 25-pin products

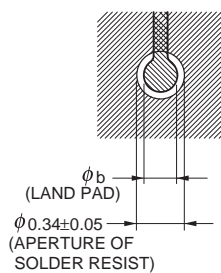
R5F10E8AALA, R5F10E8CALA, R5F10E8DALA, R5F10E8EALA

<R>	JEITA Package Code	RENESAS Code	Previous Code	MASS (Typ) [g]
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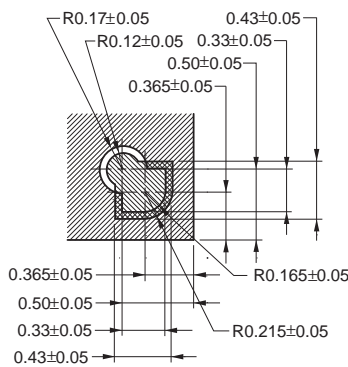
Unit: mm



DETAIL OF © PART



DETAIL OF © PART



ITEM	DIMENSIONS
D	3.00±0.10
E	3.00±0.10
w	0.20
e	0.50
A	0.69±0.07
b	0.24±0.05
x	0.05
y	0.08
y1	0.20
ZD	0.50
ZE	0.50

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